Transistors

2.5V Drive Nch MOS FET **RJK005N03**

Structure

Silicon N-channel MOS FET

Features

- 1) Low On-resistance.
- 2) Low voltage drive (2.5V drive).

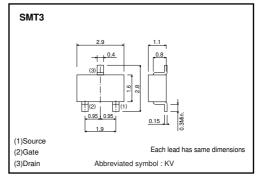
Applications

Switching

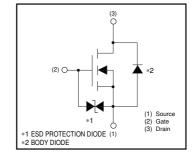
Packaging specifications and hre

	Package	Taping	
Туре	Code	T146	
	Basic ordering unit (pieces)	3000	
RJK005N03	0		

•External dimensions (Unit : mm)



Inner circuit



●Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit
Drain-source voltage		VDSS	30	V
Gate-source voltage		Vgss	±12	V
Drain current	Continuous	lD	±500	mA
Drain current	Pulsed	DP *1	±2.0	А
Source current	Continuous	ls	200	mA
(Body Diode)	Pulsed	Isp *1	800	mA
Total power dissipation		Po *2	200	mW
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	-55 to +150	°C

*1 Pw≤10µs, Duty cycle≤1%
*2 Each terminal mounted on a recommended land

Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	Rth(ch-a)*	625	°C/W

* Each terminal mounted on a recommended land



Transistors

•Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
Gate-source leakage	lgss	-	-	±10	μA	Vgs=±12V, Vds=0V	
Drain-source breakdown voltage	V(BR) DSS	30	-	-	V	I _D = 1mA, V _{GS} =0V	
Zero gate voltage drain current	IDSS	-	-	1	μA	V _{DS} = 30V, V _{GS} =0V	
Gate threshold voltage	V _{GS (th)}	0.8	-	1.5	V	V _{DS} = 10V, I _D = 1mA	
Static drain-source on-state resistance		-	400	580	mΩ	I _D = 500mA, V _{GS} = 4.5V	
	RDS (on)*	-	420	600	mΩ	I _D = 500mA, V _{GS} = 4V	
		-	650	940	mΩ	I _D = 500mA, V _{GS} = 2.5V	
Forward transfer admittance	Y _{fs} *	0.5	-	-	S	V _{DS} = 10V, I _D = 500mA	
Input capacitance	Ciss	-	60	_	pF	V _{DS} = 10V	
Output capacitance	Coss	_	24	_	pF	Vgs=0V	
Reverse transfer capacitance	Crss	-	12	-	pF	f=1MHz	
Turn-on delay time	td (on) *	-	9	-	ns	Vdd≒ 15V	
Rise time	tr *	-	11	-	ns	$I_D = 250 \text{mA}$	
Turn-off delay time	td (off) *	-	16	-	ns	- V _{GS} = 4V _ R∟=60Ω	
Fall time	t _f *	-	31	-	ns	$R_{G}=10\Omega$	
Total gate charge	Qg *	-	2.0	4.0	nC	V _{DD} =24V	
Gate-source charge	Q _{gs} *	-	0.6	-	nC	V _{GS} =4V	
Gate-drain charge	Q _{gd} *	_	0.7	_	nC	I _D = 500mA	

•Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	Vsd*	-	-	1.2	V	I _S = 500mA, V _{GS} =0V
*Pulsed						

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